

**High Voltage Trench Schottky Diode****FEATURES**

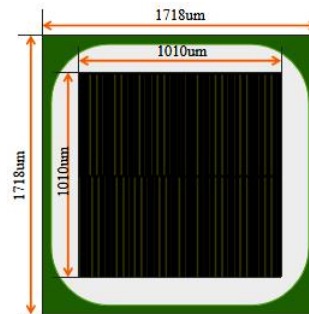
- Trench MOS Schottky technology
- Die in 6" Wafer Form
- 100V, 5A*
- $V_F=0.60V(\text{typ.})^{**}$

Electrical Characteristics ($T_j=25^\circ\text{C}$)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V_{RRM}	Maximum repetitive peak reverse voltage	105	117	—	V	$I_R=500\mu\text{A}$
V_F	Static Forward Voltage	—	0.42	0.48	V	$I_F=1\text{A}$
		—	0.52	0.62	V	$I_F=3\text{A}$
		—	0.60	0.66	V	$I_F=5\text{A}$
I_R^{***}	Cathode-to-anode Leakage Current	—	6	30	μA	$V_R=100\text{V}$
T_j, T_{STG}	Operating and Storage Temperature Range	-55°C to 150°C Max				
*** Pulse width < 300 uS, Duty cycle < 2%						

Mechanical Data

Die Size	1778×1778	μm^2	CHIP DRAWING (Scribe Line is Excluded)
Source Pad Size	1010×1010	μm^2	
Scribe Line Size	60	μm	
Wafer Diameter	6	in	
Wafer Thickness	250	μm	
Estimated Gross Die	5062(Yield>98%)		
Anode Metal Thickness	AlSiCu(5.5 μm)		
Cathode Metal Thickness	Ti\Ni\Ag(0.2 μm /0.3 μm /2 μm)		
Recommended Storage Environment	Store in original container, in dry nitrogen, < 6 months at an ambient temperature of 23°C±3°C >		



* Electrical characteristics are reported for the reference packaged part (TO-220) and can not be guaranteed in die sales form.

** Electrical characteristics are reported for the bare die. Variations in customer packaging materials, dimensions and processes may affect parametric performance.